



## INA-01100 Absolute Maximum Ratings

Parameter	Absolute Maximum <sup>[1]</sup>
Device Current	50 mA
Power Dissipation <sup>[2,3]</sup>	400 mW
RF Input Power	+13 dBm
Junction Temperature	200°C
Storage Temperature	-65 to 200°C

### Thermal Resistance:

$$\theta_{jc} = 60^{\circ}\text{C/W}$$

### Notes:

1. Permanent damage may occur if any of these limits are exceeded.
2.  $T_{\text{Mounting Surface}} (T_{\text{MS}}) = 25^{\circ}\text{C}$ .
3. Derate at 16.7 mW/°C for  $T_{\text{MS}} > 176^{\circ}\text{C}$ .

## INA-01100 Electrical Specifications<sup>[1,3]</sup>, $T_A = 25^{\circ}\text{C}$

Symbol	Parameters and Test Conditions <sup>[2]</sup> : $I_d = 35 \text{ mA}$ , $Z_o = 50 \Omega$	Units	Min.	Typ.	Max.
G <sub>P</sub>	Power Gain ( $ S_{21} ^2$ ) f = 100 MHz	dB		32.5	
$\Delta G_P$	Gain Flatness f = 10 to 250 MHz	dB		±0.5	
f <sub>3 dB</sub>	3 dB Bandwidth	MHz		500	
ISO	Reverse Isolation ( $ S_{12} ^2$ ) f = 10 to 250 MHz	dB		39	
VSWR	Input VSWR f = 10 to 250 MHz			1.6:1	
	Output VSWR f = 10 to 250 MHz			1.5:1	
NF	50 $\Omega$ Noise Figure f = 100 MHz	dB		1.7	
P <sub>1 dB</sub>	Output Power at 1 dB Gain Compression f = 100 MHz	dBm		11	
IP <sub>3</sub>	Third Order Intercept Point f = 100 MHz	dBm		23	
t <sub>D</sub>	Group Delay f = 100 MHz	psec		200	
V <sub>d</sub>	Device Voltage	V	4.0	5.5	7.0
dV/dT	Device Voltage Temperature Coefficient	mV/°C		+10	

### Notes:

1. The recommended operating current range for this device is 30 to 40 mA. Typical performance as a function of current is on the following page.
2. RF performance of the chip is determined by packaging and testing 10 devices per wafer.
3. The values are the achievable performance for the INA-01100 mounted in a 70 mil stripline package.

## INA-01100 Typical Scattering Parameters<sup>[1]</sup> ( $Z_o = 50 \Omega$ , $T_A = 25^{\circ}\text{C}$ , $V_{CC} = 35 \text{ mA}$ )

Freq. GHz	S <sub>11</sub>		S <sub>21</sub>			S <sub>12</sub>			S <sub>22</sub>		k
	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang	
0.01	0.09	-16	32.7	43.4	-1	-38.5	.012	-1	.18	1	1.17
0.05	0.10	-27	32.7	43.1	-10	-38.6	.012	15	.19	5	1.18
0.10	0.11	-5	32.4	41.9	-20	-38.4	.012	-8	.20	10	1.17
0.20	0.14	-80	31.6	38.0	-37	-38.6	.012	4	.24	14	1.22
0.30	0.18	-98	30.5	33.7	-52	-38.8	.011	-10	.27	15	1.31
0.40	0.20	-110	29.4	29.6	-65	-39.6	.011	2	.30	10	1.51
0.50	0.22	-115	28.4	26.2	-75	-38.6	.012	-12	.32	6	1.48
0.60	0.24	-120	27.4	23.4	-84	-39.1	.011	-7	.34	1	1.67
0.80	0.27	-124	25.7	19.3	-100	-38.3	.012	-6	.36	-11	1.76
1.00	0.30	-127	24.3	16.3	-115	-36.1	.016	-5	.36	-22	1.58
1.5	0.44	165	21.8	12.37	-179	-33.6	.020	42	.19	-69	1.75
2.0	0.44	154	17.9	7.88	146	-33.0	.022	42	.13	-106	2.42
2.5	0.46	148	14.6	5.36	121	-30.6	.029	36	.12	-151	2.63
3.0	0.48	139	11.4	3.71	96	-30.0	.032	45	.10	159	3.31

### Note:

1. S-parameters are de-embedded from 70 mil package measured data using the package model found in the DEVICE MODELS section of the *Communications Components Designer's Catalog*.

## INA-01100 Typical Performance, $T_A = 25^\circ\text{C}$

(unless otherwise noted: The values are the achievable performance for the INA-01100 mounted in a 70 mil stripline package.)

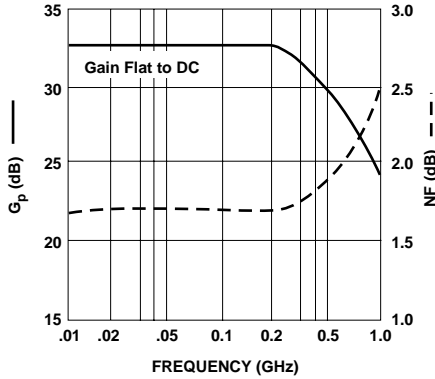


Figure 1. Typical Gain and Noise Figure vs. Frequency,  $T_A = 25^\circ\text{C}$ ,  $I_d = 35\text{ mA}$

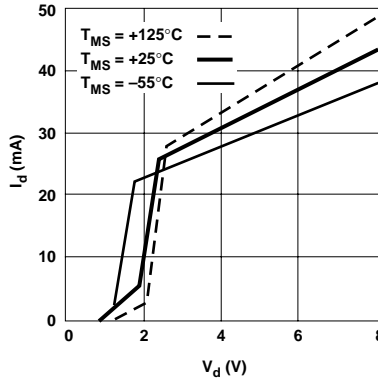


Figure 2. Device Current vs. Voltage.

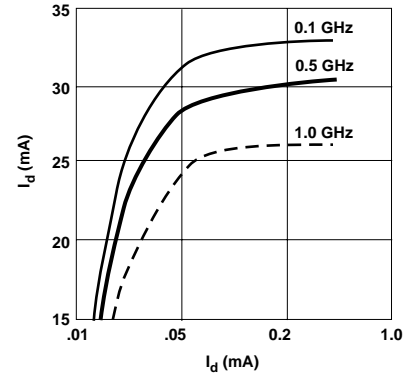


Figure 3. Power Gain vs. Current.

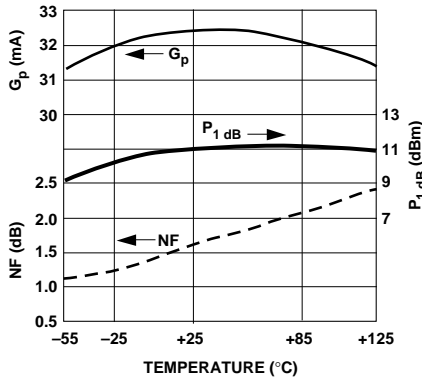


Figure 4. Output Power and 1 dB Gain Compression, NF and Power Gain vs. Case Temperature.  $f = 0.1\text{ GHz}$ ,  $I_d = 35\text{ mA}$ .

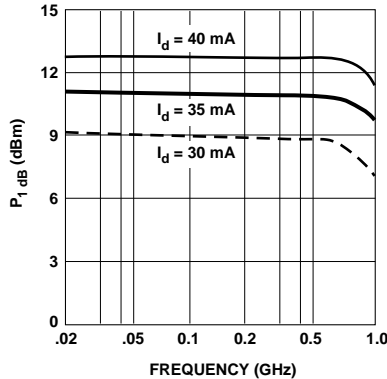


Figure 5. Output Power at 1 dB Gain Compression vs. Frequency.

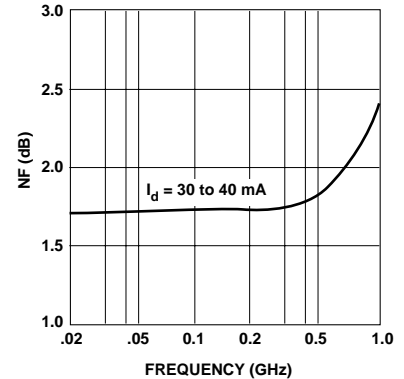
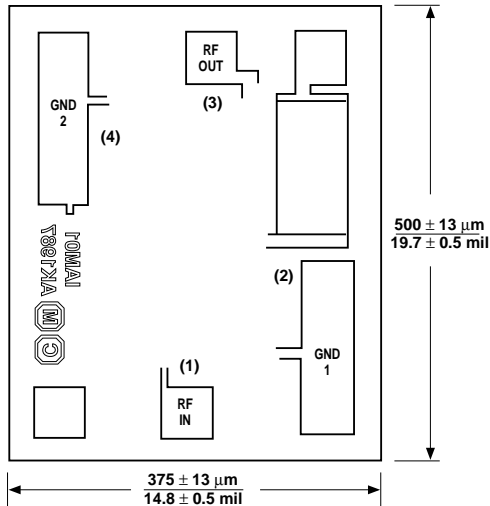


Figure 6. Noise Figure vs. Frequency.

## INA-01100 Chip Dimensions



Chip thickness is  $140\ \mu\text{m}/5.5\text{ mil}$ . Bond Pads are  $41\ \mu\text{m}/1.6\text{ mil}$  typical on each side. Note: Ground Bonding is Critical. Refer to Application Bulletin, "AB-0007: INA Bonding Configuration".